

Title (en)  
METHOD FOR MANUFACTURING A MASK HAVING SUBMILLIMETRIC APERTURES FOR A SUBMILLIMETRIC ELECTRICALLY CONDUCTIVE GRID, AND MASK AND SUBMILLIMETRIC ELECTRICALLY CONDUCTIVE GRID

Title (de)  
VERFAHREN ZUR HERSTELLUNG EINER MASKE MIT SUBMILLIMETRISCHEN ÖFFNUNGEN FÜR EIN SUBMILLIMETRISCHES ELEKTRISCH LEITFÄHIGES GITTER UND MASKE UND SUBMILLIMETRISCHES ELEKTRISCH LEITFÄHIGES GITTER

Title (fr)  
PROCEDE DE FABRICATION D'UN MASQUE A OUVERTURES SUBMILLIMETRIQUES POUR GRILLE ELECTROCONDUCTRICE SUBMILLIMETRIQUE, MASQUE ET GRILLE ELECTROCONDUCTRICE SUBMILLIMETRIQUE

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• FR 0856429 A 20080924

Abstract (en)  
[origin: WO2010034945A1] The invention relates to a method for manufacturing a mask having submillimetric apertures (1, 10), wherein: a first solution of colloidal nanoparticles in a first solvent is deposited for a mask layer, the particles having a given vitreous transition temperature T<sub>g</sub>; the mask layer, referred to as the first mask layer, is dried at a temperature lower than said temperature T<sub>g</sub> until a mask having a two-dimensional array of submillimetric apertures is obtained, having a substantially straight edge and defining a so-called array mask area; a solid mask area is formed through liquid deposition of a second mask layer onto the surface thereof, the solid mask area being adjacent and contacting the array mask area; and/or at least one cache area is formed, said cache area contacting the array mask area; and/or a mask area, filled through liquid filling of the apertures of a part of the array mask area, is formed after drying the first mask layer. The invention also relates to the mask and to the electrically conductive grid thus obtained.

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